

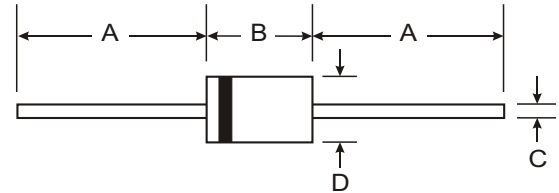
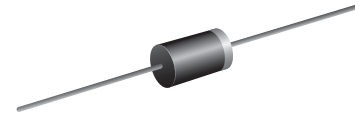
VOLTAGE RANGE: 20 - 100V
CURRENT: 1.0 A

Features

- Schottky Barrier Chip
- Guard Ring Die Construction for Transient Protection
- High Current Capability
- Low Power Loss, High Efficiency
- High Surge Current Capability
- For Use in Low Voltage, High Frequency Inverters, Free Wheeling, and Polarity Protection Applications

Mechanical Data

- Case: DO-41, Molded Plastic
- Terminals: Plated Leads Solderable per MIL-STD-202, Method 208
- Polarity: Cathode Band
- Weight: 0.34 grams (approx.)
- Mounting Position: Any
- Marking: Type Number



DO-41		
Dim	Min	Max
A	25.40	—
B	4.06	5.21
C	0.71	0.864
D	2.00	2.72
All Dimensions in mm		

Maximum Ratings and Electrical Characteristics T_A = 25°C unless otherwise specified

Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Characteristic	Symbol	MBR120	MBR130	MBR140	MBR150	MBR160	MBR180	MBR1100	Unit		
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	20	30	40	50	60	80	100	V		
RMS Reverse Voltage	V _{R(RMS)}	14	21	28	35	42	56	70	V		
Average Rectified Output Current @T _L = 100°C (Note 1)	I _O	1.0							A		
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	I _{FSM}	40							A		
Forward Voltage @I _F = 1.0A	V _{FM}	0.50			0.70		0.85		V		
Peak Reverse Current @T _A = 25°C At Rated DC Blocking Voltage @T _A = 100°C	I _{RM}	0.5					10			mA	
Typical Junction Capacitance (Note 2)	C _j	110			80				pF		
Typical Thermal Resistance (Note 1)	R _{θJL} R _{θJA}	15					50				°C/W
Operating and Storage Temperature Range	T _j , T _{STG}	-65 to +150							°C		

Note: 1. Valid provided that leads are kept at ambient temperature at a distance of 9.5mm from the case.

2. Measured at 1.0 MHz and applied reverse voltage of 4.0V D.C.

RATINGS AND CHARACTERISTIC CURVES MBR120 THRU MBR1100

